

## N-Channel Power MOSFET

600V, 38A, 99mΩ

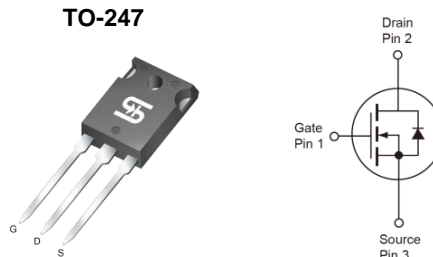
### FEATURES

- Super-Junction technology
- High performance, small  $R_{DS(on)} * Q_g$  figure of merit (FOM)
- High ruggedness performance
- 100% UIS and  $R_g$  tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
$V_{DS}$	600	V
$R_{DS(on)}$ (max)	99	mΩ
$Q_g$	62	nC

### APPLICATIONS

- PFC stage
- Server/Telecom Power
- Charging Station
- Inverter
- Power Supply



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	38
		$T_C = 100^\circ\text{C}$	24
Pulsed Drain Current (Note 2)	$I_{DM}$	114	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	329	W
Single Pulse Avalanche Energy (Note 3)	$E_{AS}$	784	mJ
Single Pulse Avalanche Current (Note 3)	$I_{AS}$	5.6	A
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	0.38	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	42	$^\circ\text{C/W}$

**Thermal Performance Note:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	$BV_{DSS}$	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	$I_{DSS}$	--	--	1	$\mu\text{A}$
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10\text{V}, I_D = 11.7\text{A}$	$R_{DS(on)}$	--	86	99	m $\Omega$
<b>Dynamic</b> (Note 5)						
Total Gate Charge	$V_{DS} = 480\text{V}, I_D = 35\text{A}, V_{GS} = 10\text{V}$	$Q_g$	--	62	--	nC
Gate-Source Charge		$Q_{gs}$	--	17	--	
Gate-Drain Charge		$Q_{gd}$	--	25	--	
Input Capacitance	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	$C_{iss}$	--	2587	--	pF
Output Capacitance		$C_{oss}$	--	123	--	
Reverse Transfer Capacitance		$C_{rss}$	--	20	--	
Gate Resistance	$f = 1.0\text{MHz}$	$R_g$	--	3.3	6.6	$\Omega$
<b>Switching</b> (Note 6)						
Turn-On Delay Time	$V_{DD} = 300\text{V}, R_{GEN} = 5\Omega, I_D = 17.5\text{A}, V_{GS} = 10\text{V},$	$t_{d(on)}$	--	18	--	ns
Turn-On Rise Time		$t_r$	--	24	--	
Turn-Off Delay Time		$t_{d(off)}$	--	87	--	
Turn-Off Fall Time		$t_f$	--	25	--	
<b>Source-Drain Diode</b>						
Body-Diode Continuous Forward Current		$I_S$	--	--	38	A
Body-Diode Pulsed Current		$I_{SM}$	--	--	114	A
Forward Voltage (Note 4)	$I_S = 35\text{A}, V_{GS} = 0\text{V}$	$V_{SD}$	--	--	1.4	V
Reverse Recovery Time	$I_S = 17.5\text{A}$	$t_{rr}$	--	342	--	ns
Reverse Recovery Charge		$dI_F/dt = 100\text{A}/\mu\text{s}$	$Q_{rr}$	--	5.3	--

**Notes:**

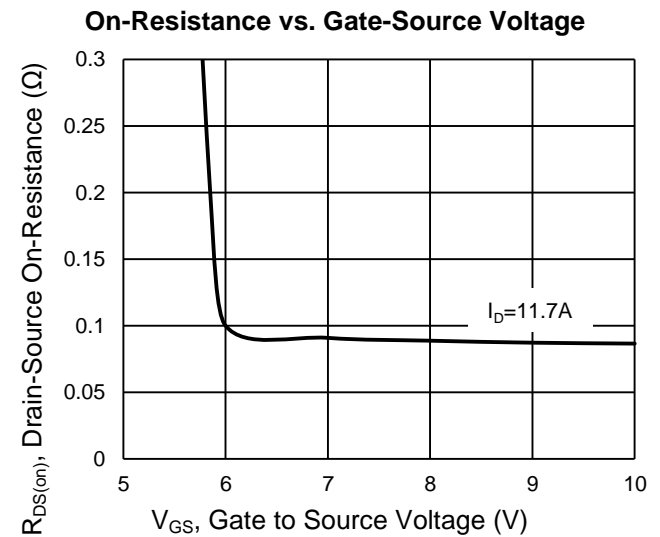
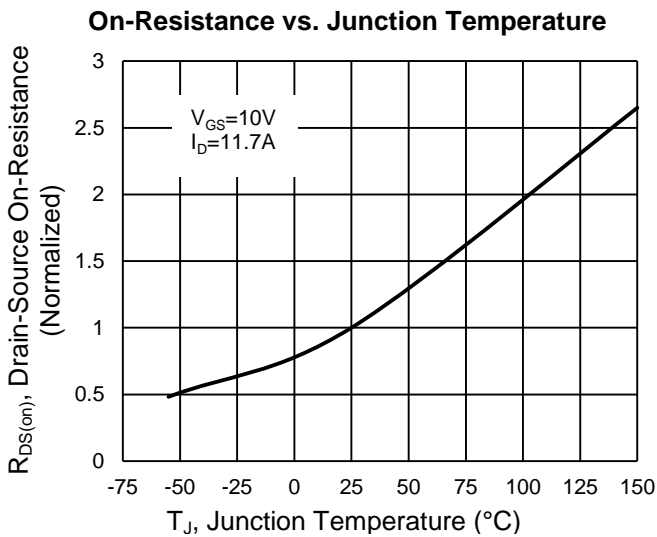
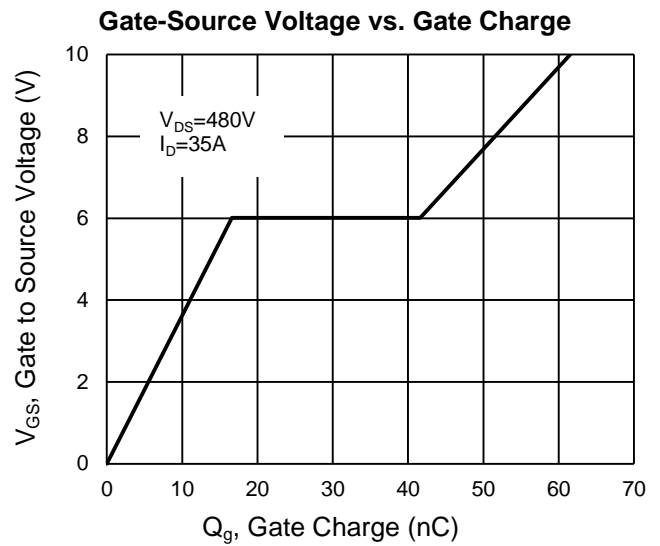
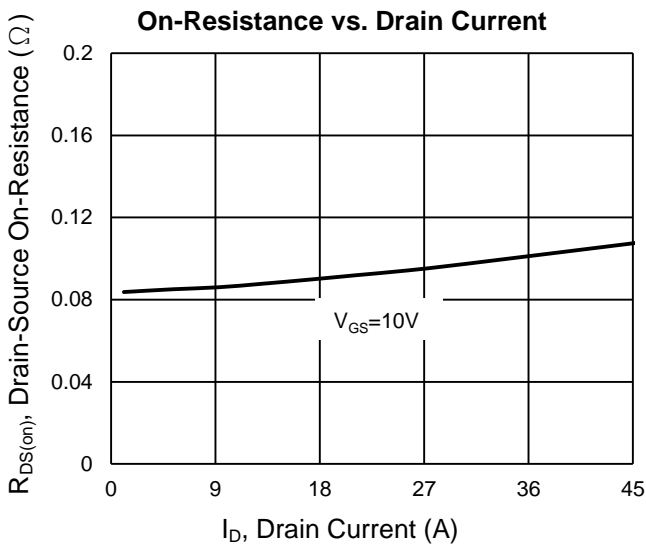
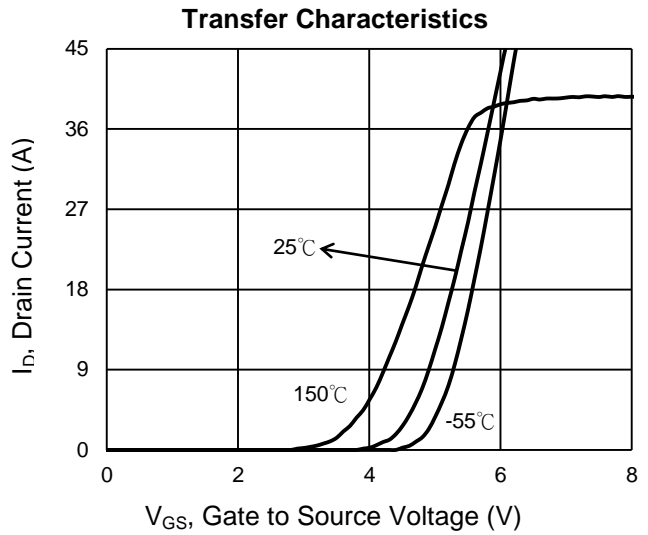
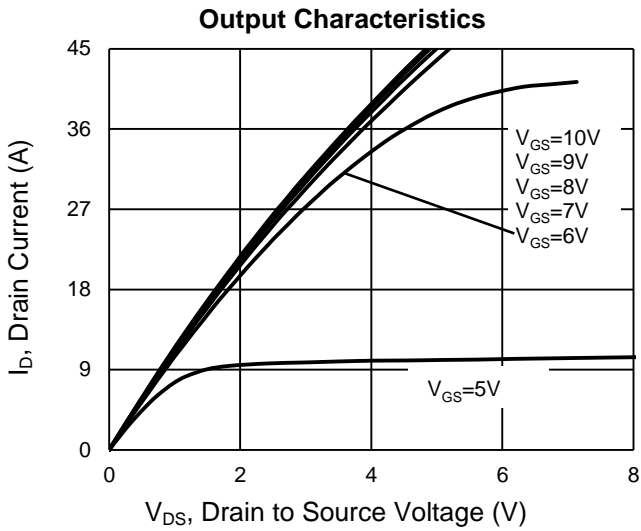
- Current limited by package.
- Pulse width limited by the maximum junction temperature.
- $L = 50\text{mH}, I_{AS} = 5.6\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
- Pulse test:  $PW \leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

**ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM60NB099PW C1G	TO-247	25pcs / Tube

**CHARACTERISTICS CURVES**

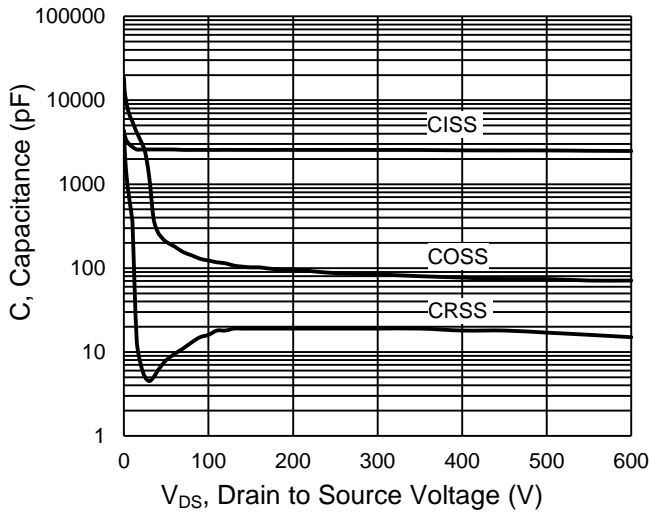
( $T_c = 25^\circ\text{C}$  unless otherwise noted)



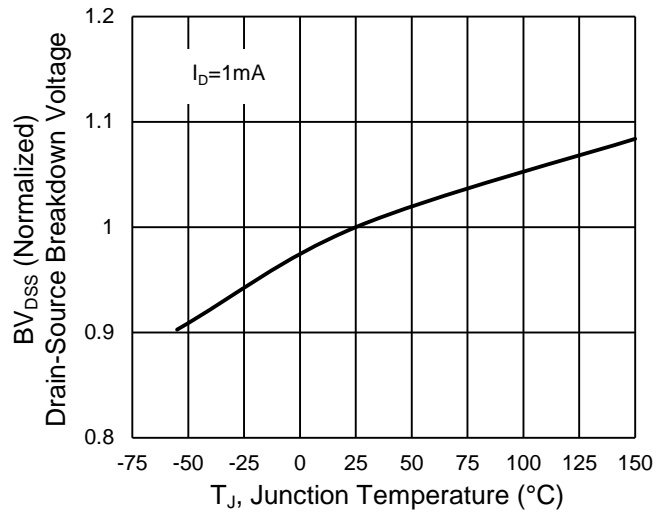
**CHARACTERISTICS CURVES**

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

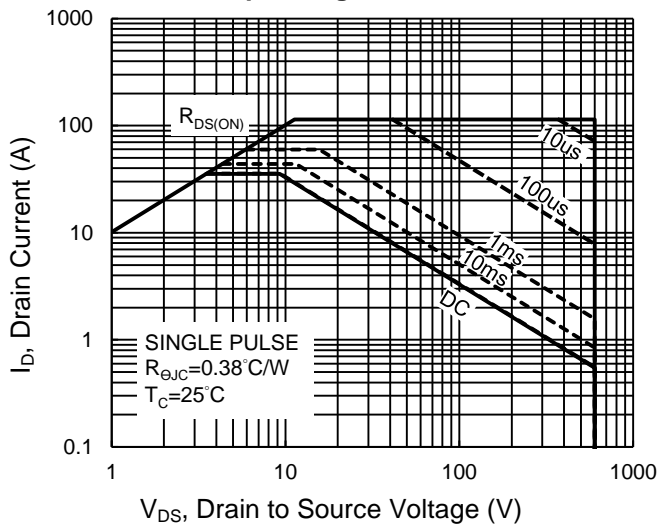
**Capacitance vs. Drain-Source Voltage**



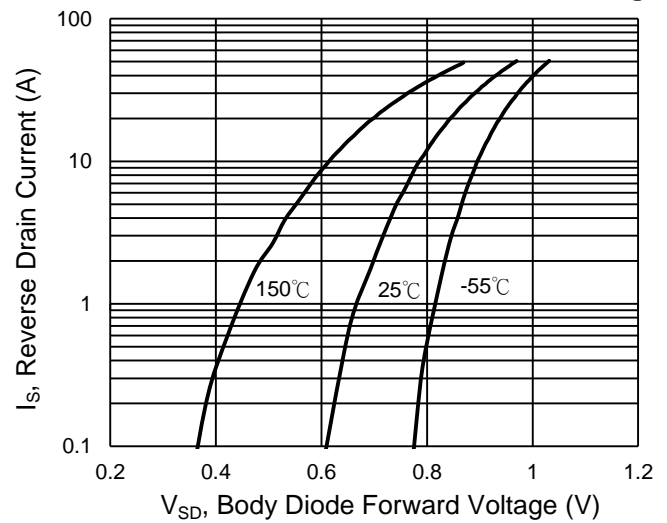
**$BV_{DSS}$  vs. Junction Temperature**



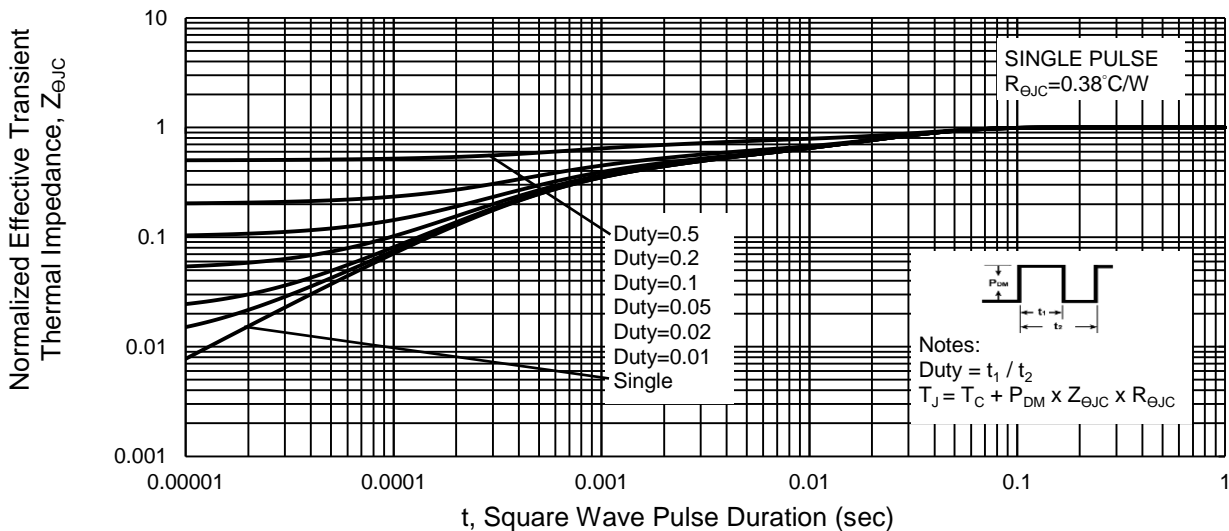
**Maximum Safe Operating Area, Junction-to-Case**



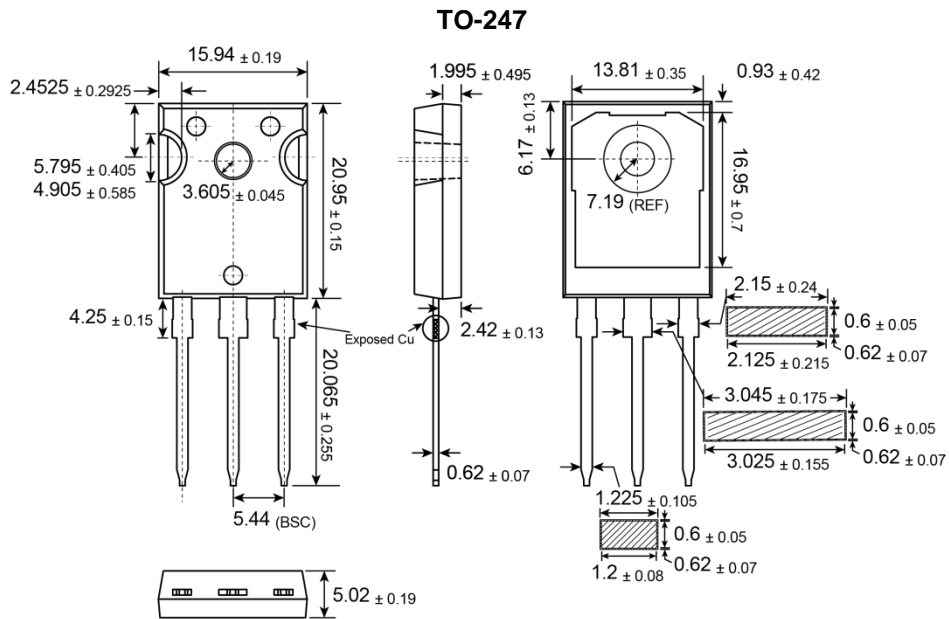
**Source-Drain Diode Forward Current vs. Voltage**



**Normalized Thermal Transient Impedance, Junction-to-Case**



**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)



**MARKING DIAGRAM**



- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

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